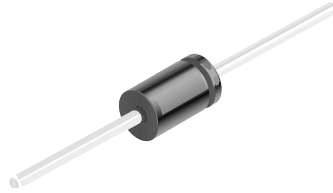


1N457/A



DO-35

Color Band Denotes Cathode

Small Signal Diode

Absolute Maximum Ratings*

$T_A = 25^\circ\text{C}$ unless otherwise noted

Symbol	Parameter	Value	Units
V_{RRM}	Maximum Repetitive Reverse Voltage	70	V
$I_{F(AV)}$	Average Rectified Forward Current	200	mA
I_{FSM}	Non-repetitive Peak Forward Surge Current Pulse Width = 1.0 second Pulse Width = 1.0 microsecond	1.0 4.0	A A
T_{stg}	Storage Temperature Range	-65 to +200	$^\circ\text{C}$
T_J	Operating Junction Temperature	175	$^\circ\text{C}$

*These ratings are limiting values above which the serviceability of any semiconductor device may be impaired.

NOTES:

- 1) These ratings are based on a maximum junction temperature of 200 degrees C.
- 2) These are steady state limits. The factory should be consulted on applications involving pulsed or low duty cycle operations.

Thermal Characteristics

Symbol	Parameter	Value	Units
P_D	Power Dissipation	500	mW
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient	300	$^\circ\text{C/W}$

Electrical Characteristics

$T_A = 25^\circ\text{C}$ unless otherwise noted

Symbol	Parameter	Test Conditions	Min	Max	Units
V_R	Breakdown Voltage	$I_R = 100 \mu\text{A}$	70		V
V_F	Forward Voltage	$I_F = 20 \text{ mA}$		1.0	V
		$I_F = 100 \text{ mA}$		1.0	V
I_R	Reverse Current	$V_R = 60 \text{ V}$		25	nA
		$V_R = 60 \text{ V}, T_A = 150^\circ\text{C}$		5	μA
C_T	Total Capacitance	$V_R = 0, f = 1.0 \text{ MHz}$		8.0	pF